IN THE CLAIMS

Please amend the claims as follows:

Assignce: Raythcon Company

- 1. (Previously Presented) A surface-heating system comprising:
- a frequency generator to generate a millimeter-wave frequency; and
- an <u>active reflect-array</u> antenna system to provide a collimated high-power wavefront at the <u>a</u> millimeter-wave frequency in a direction of a surface to heat the surface within a surface depth by reflecting a spatially-fed millimeter-wave lower-power wavefront; and
- a low-power feed to provide the spatially-fed millimeter-wave lower-power wavefront for incident on the active reflect-array.
- (Currently Amended) The system of claim 1 wherein the <u>active reflect-array</u> antenna system comprises an active array having a plurality of <u>individual</u> semiconductor wafers arranged together on a surface, wherein each semiconductor wafer comprises:
- a receive antenna to receive signals of the spatially-fed millimeter-wave lower-power wavefront;
- <u>a one or more</u> sets of power amplifiers <u>coupled to the receive antenna</u> to amplify the <u>received signals-millimeter-wave frequency;</u> and
- one or more a transmit antennas to transmit amplified millimeter-wave signals,
 wherein the amplified millimeter-wave signals transmitted by the transmit antennas of
 each semiconductor wafer spatially combine to generate the collimated high-power wavefront,
 wherein each set of power amplifiers is associated with one of the transmit antennas.
- (Cancelled) The system of claim 2 wherein the active array is an active reflect array to
 receive a spatially fed millimeter wave lower power wavefront, to amplify the lower power
 wavefront, and to generate the high power wavefront.

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111 Serial Number: 10/693 125

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(Currently Amended) The system of claim 2.3 wherein the plurality of semiconductor wafers is arranged in a substantially parabolic shape, and each semiconductor wafer includes:
 one or more receive antennas to receive the spatially fed millimeter wave lower power wavefront:

one or more sets of power amplifiers to amplify signals of the spatially fed millimeterwave lower-power-wavefront; and

one or more transmit antennas to transmit the amplified signals to generate the collimated high-power-wavefront.

wherein each set of power-amplifiers is associated with one of the transmit and one of the receive antennas

- (Cancelled) The system of claim 3 further comprising a low-power feed to provide the lower-power wavefront at the millimeter-wave frequency for incident on the active reflect-array.
- (Currently Amended) The system of claim 2 <u>further comprising a frequency generator</u> to generate the <u>millimeter-wave frequency</u> and provide the <u>millimeter-wave frequency</u> to the <u>low-power feed.</u>

wherein the frequency generator and the active reflect-array antenna system are part of a wavefront-generating subsystem, the system further comprising a thermal-sensing subsystem to measure a surface temperature and generate a control signal for the wavefront-generating subsystem to control the surface temperature.

- 7. (Currently Amended) The system of claim 6 wherein the <u>active reflect-array</u> antenna system generates a continuous-wave wavefront, and wherein the antenna system changes a transmit power level of the wavefront in response to the control signal from the thermal-sensing subsystem to control the surface temperature.
- 8. (Currently Amended) The system of claim 6 wherein the <u>active reflect-array</u> antenna system generates a pulsed high-power wavefront, and wherein the antenna system reduces one of

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either a pulse-repetition-rate or a pulse-duration time of the high-power wavefront in response to the control signal to control the surface temperature.

(Currently Amended) The system of claim 2 further comprising a housing having a cavity for placement of a food item, and

wherein the active <u>reflect-array antenna system</u> is one of a plurality of active <u>reflect-array antenna systems</u> positioned within the cavity to direct a plurality of high-power millimeter-wave wavefronts within the cavity to heat a surface of the food item.

- 10. (Original) The system of claim 9 further comprising a microwave amplifier and associated antenna to direct microwave energy within the cavity to heat the food item below the surface.
- 11. (Currently Amended) The system of claim 1 5 wherein the active reflect-array antenna system is a first active reflect-array antenna system and the low-power feed is a second active reflect-array antenna system.

wherein the low-power feed amplifies and reflects millimeter-wave signals received from a source <u>located</u> within of the <u>first</u> active reflect-array <u>antenna system</u>, the low-power feed comprising:

one or more receive antennas to receive the millimeter-wave signals from the source; one or more amplifiers to amplify the received millimeter-wave frequency signals; and one or more transmit antennas to transmit the amplified millimeter-wave signals and generate the lower-power wavefront for incidence on the <u>first</u> active reflect-array <u>antenna</u> system.

12. (Currently Amended) The system of claim 3 2 wherein the low-power feed comprises further comprising a passive reflector to reflect a millimeter-wave frequency signal from a feed and provide the lower-power wavefront for incident on the active reflect-array antenna system.

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13. (Original) The system of claim 2 wherein the plurality of semiconductor wafers is arranged on a substantially flat surface.

- 14. (Currently Amended) The system of claim 2 further comprising
- a low-voltage, high-current power supply to generate current for the active <u>reflect-</u>aπay antenna system and a frequency generator: and

a cooling subsystem to cool the active <u>reflect-array antenna system</u> and the power supply, wherein the cooling system comprises one of either a thermo-electric-cooling (TEC) element, a phase change fluid, or coolant.

 (Currently Amended) A millimeter-wave surface-heating system comprising: The system of claim 1 wherein the antenna system is a passive reflect array antenna system and comprises:

a high-power amplifier to generate a high-power millimeter-wave frequency-signal; a reflector to reflect a the high-power millimeter-wave signal; and

a passive reflect<u>-array</u> antenna to receive the reflected high-power <u>millimeter-wave</u> signal and re-transmit the signal to <u>generate the provide a</u> collimated high-power wavefront,

wherein the passive reflect-array antenna comprises a plurality of dual-polarized dipoles of varying sizes arranged circumferentially in a substantially flat surface to operate as a parabolic surface to provide the collimated high-power wavefront at a millimeter-wave frequency in a direction of a surface to heat the surface, and

wherein the reflector provides a spatially-fed millimeter-wave wavefront for incidence on the passive reflect-array antenna.

16. (Currently Amended) The system of claim 15-wherein the passive reflect antenna is comprised of a plurality of dual-polarized dipoles of varying sizes arranged-circumferentially in a substantially flat surface-further comprising a high-power amplifier to generate the high-power millimeter-wave frequency signal.

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17. (Currently Amended) The system of claim 4 6 wherein the frequency generator is configured to generate a plurality of differing millimeter-wave frequencies, and

wherein the <u>active reflect-array</u> antenna system provides the high-power wavefront comprising the differing millimeter-wave frequencies, and

wherein the system further comprises a system controller to control a frequency and power level of the wavefront to selectively heat layers of the surface.

- 18. (Currently Amended) The system of claim 17 wherein the high-power wavefront comprising the differing millimeter-wave-frequencies is time-multiplexed with differing millimeter-wave frequencies.
- (Cancelled) The system of claim 1 wherein the antenna system is configured to provide the collimated high power wavefront.
 - 20. (Withdrawn) A system for browning food comprising:
 - a housing having a cavity; and
- a plurality of active-arrays within the cavity to direct a plurality of high-power millimeter-wave wavefronts within the cavity to heat a surface of a food item placed therein,

wherein the wavefronts are either collimated or converging high-power wavefronts at a millimeter-wave frequency.

21. (Withdrawn) The system of claim 20 wherein active arrays have a plurality of semiconductor wafers arranged on a substantially flat surface, wherein each semiconductor wafer comprises:

one or more sets of power amplifiers to amplify a millimeter-wave frequency signal; and one or more transmit antennas to generate either the collimated or converging high-power wavefronts.

wherein each set of power amplifiers is associated with one of the transmit antennas.

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22. (Withdrawn) The system of claim 20 further comprising:

a thermal-sensing subsystem to measure a surface temperature of the food item and generate a control signal to maintain the surface temperature substantially within a predetermined temperature range; and

a microwave amplifier and associated antenna to direct microwave energy within the cavity to heat the food item below the surface.

- 23. (Withdrawn) The system of claim 22 wherein the active arrays generate a continuouswave wavefront, and wherein a transmit power level of the wavefront is changed in response to the control signal from the thermal-sensing subsystem to control the surface temperature.
- 24. (Withdrawn) The system of claim 22 wherein the active arrays generate a pulsed high-power wavefront, and wherein one of either a pulse-repetition-rate or a pulse-duration time of the high-power wavefront is changed in response to the control signal to control the surface temperature.
- 25. (Withdrawn) The system of claim 20 further comprising a frequency generator to generate a plurality of differing millimeter-wave frequencies, and wherein the active arrays provide the high-power wavefronts comprising the differing millimeter-wave frequencies, and wherein the system further comprises a system controller to control a frequency and power level of the wavefronts to selectively heat layers of the surface.
- 26. (Withdrawn) The system of claim 25 wherein the high-power wavefronts comprising the differing millimeter-wave frequencies are time-multiplexed with the differing millimeterwave frequencies.
 - 27. (Withdrawn) A system for removing paint on a surface comprising:
 - a frequency generator to generate a millimeter-wave frequency; and

an antenna system to provide either a collimated or converging high-power wavefront at the millimeter-wave frequency in a direction of a surface to heat the surface to within a surface depth,

wherein the antenna system comprises an active array having a plurality of semiconductor wafers arranged on a surface, wherein each semiconductor wafer comprises:

one or more sets of power amplifiers to amplify the millimeter-wave frequency; and one or more transmit antennas to generate either the collimated or converging high-power wavefront.

wherein each set of power amplifiers is associated with one of the transmit antennas.

28. (Withdrawn) The system of claim 27 wherein the active array is an active reflect-array to receive a spatially fed millimeter-wave lower-power wavefront, amplify the lower-power wavefront, and generate the high-power wavefront, and

wherein the plurality of semiconductor wafers is arranged in a substantially parabolic shape, and wherein each semiconductor wafer includes:

one or more receive antennas to receive the spatially fed millimeter-wave lower-power wavefront;

one or more sets of power amplifiers to amplify signals of the spatially fed millimeterwave lower-power wavefront; and

one or more transmit antennas to transmit the amplified signals to generate either the collimated or converging high-power wavefront,

wherein each set of power amplifiers is associated with one of the transmit and one of the receive antennas.

29. (Withdrawn) The system of claim 28 further comprising a thermal-sensing subsystem to measure a surface temperature and generate a control signal for the wavefront-generating subsystem to control the surface temperature.

- 30. (Withdrawn) The system of claim 29 wherein the antenna system generates a continuous-wave wavefront, and wherein the antenna system changes a transmit power level of
- the wavefront in response to the control signal from the thermal-sensing subsystem to control the surface temperature.
- 31. (Withdrawn) The system of claim 29 wherein the antenna system generates a pulsed high-power wavefront, and wherein the antenna system reduces one of either a pulse-repetition-rate or a pulse-duration time of the high-power wavefront in response to the control signal to control the surface temperature.
- 32. (Withdrawn) A method of heating a surface comprising generating either a collimated or converging high-power wavefront at the millimeter-wave frequency in a direction of a surface using a semiconductor-based active array antenna.
 - 33. (Withdrawn) The method of claim 32 further comprising:

measuring a surface temperature and generating a control signal to control the surface temperature; and

changing either a transmit power level of the wavefront, a pulse-repetition-rate of the wavefront, or a pulse-duration time of the wavefront in response to the control signal from the thermal-sensing subsystem to control the surface temperature.

34. (Withdrawn) The method of claim 33 wherein generating comprises:

receiving a spatially-fed lower-power millimeter-wave wavefront incident on an active reflect array comprising a plurality of semiconductor wafers arranged on a surface having receive antennas thereon;

amplifying signals of the received lower-power wavefront with power amplifiers on the wafers: and

retransmitting the signals of the received wavefront to generate the high-power wavefront in the direction of the surface with transmit antennas on the wafers.

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35. (Withdrawn) The method of claim 32 wherein generating comprises generating a plurality of differing millimeter-wave frequencies to provide the high-power wavefront comprising the differing millimeter-wave frequencies, and

wherein the method further comprises controlling a frequency and power level of the wavefront to selectively heat layers of the surface.

36. (Withdrawn) The method of claim 35 further comprising time-multiplexing the differing millimeter-wave frequencies of the high-power wavefront to selectively heat layers of the surface.

37. (Withdrawn) The method of claim 32 wherein generating comprises generating either the collimated high-power wavefront, the converting high-power wavefront, or a diverging highpower wavefront.